PATENT APPLICATION

S. Stevenson
10/5/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE 10-9-01

In re the Application of

Hiroji AGA, Naoto TATE,
Susumu KUWABARA, Kiyoshi MITANI

Application No.: U.S. National Stage
of PCT/JP00/07111

Filed: June 11, 2001 Docket No.: 109725

For: METHOD FOR PRODUCING SOI WAFER AND SOI WAFER

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claim 6 as follows:

6. (Amended) An SOI wafer produced by the method according to Claim 1, which has an RMS value of 0.5 nm or less concerning surface roughness for both of 1 μm square and 10 μm square.

Please add new claims 7-9 as follows:

-- 7. An SOI wafer produced by the method according to Claim 2, which has an RMS value of 0.5 nm or less concerning surface roughness for both of 1 μm square and 10 μm square. --

-- 8. An SOI wafer produced by the method according to Claim 3, which has an RMS value of 0.5 nm or less concerning surface roughness for both of 1 μm square and 10 μm square. --